



SPD900-9P

- **Stem Type PIN-Photodiode**
- **Hermetically sealed**
- **High photocurrent**
- **Si Structure**



Lead (Pb) free product – RoHS compliant

Description

SPD900-9P is a **Si based** PIN-Photodiode in hermetically sealed TO-39 STEM package. It features a 3.0x3.0mm² active area chip die offering **excellent responsivity** and **high photocurrent**. The TO-39 housing comes with gold plated cap and **flat glass lens**, giving wide angle of acceptance of $\pm 55^\circ$

Maximum Ratings [T_a=25°C]

Parameter	Symbol	Values		Unit
		Min.	Max.	
Reverse Breakdown Voltage	V _{(BR)R}		170	V
Operating Temperature	T _{OPR}	- 25	+ 100	°C
Storage Temperature	T _{STG}	- 30	+ 125	°C
Soldering Temperature	T _{SOLDER}		240	°C

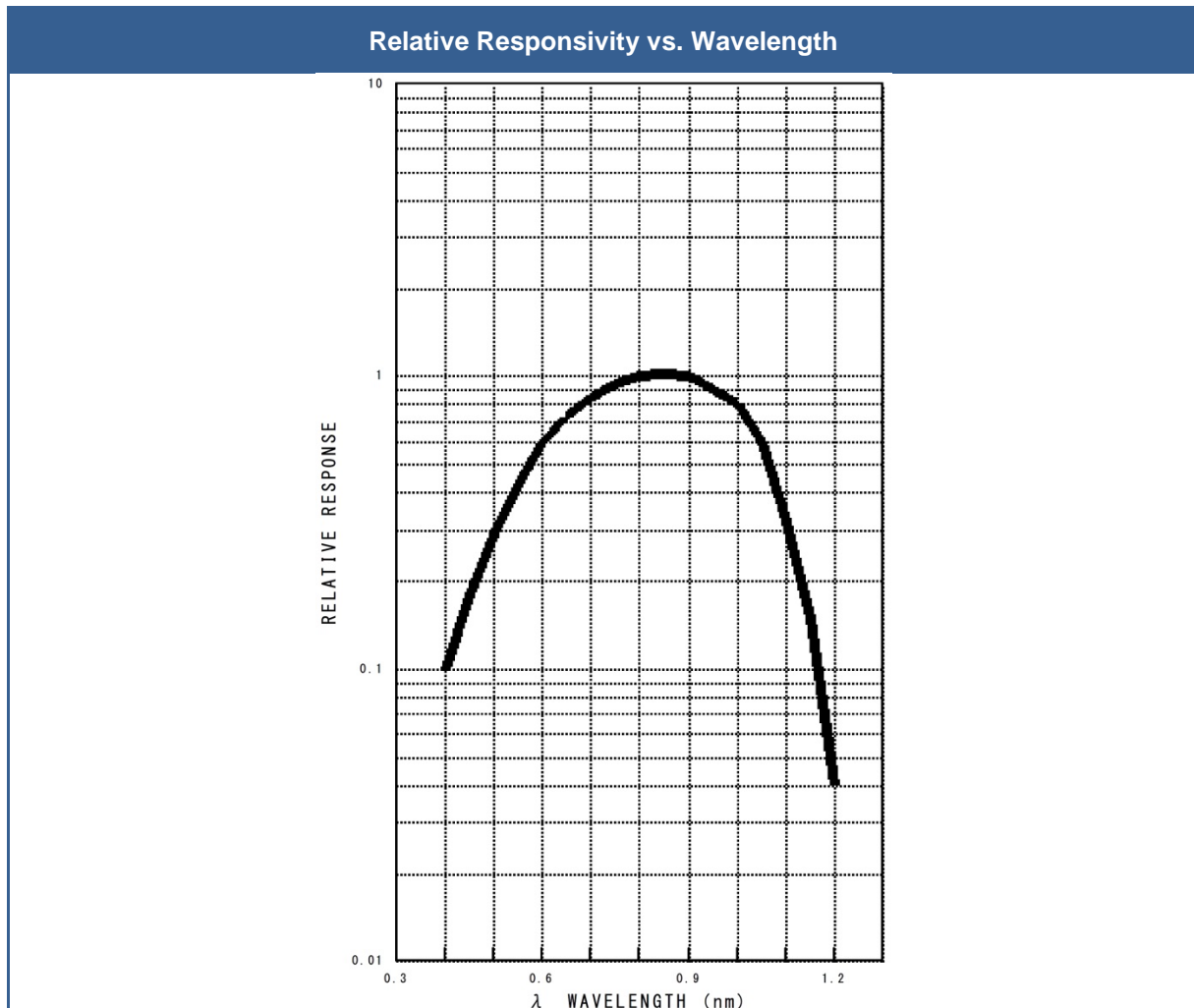
Characteristics [T_{case}=25°C]

Parameter	Symbol	Min.	Values		Unit
			Typ.	Max.	
Reverse Photo Current (V _R =10V, L=1000Lx)	I _L		110		µA
Reverse Dark Current (V _R =10V)	I _D		5	30	nA
Open Circuit Voltage (V _R =10V, L=1000Lx)	V _{OC}		350		mV
Spectral Responsivity (Peak)	λ _P		900		nm
Half Angle of sensitivity	θ _{1/2}		±50		deg.
Total Capacitance (V _R =10V, f=1Mhz)	C _T		25		pF
Rise time (10%-90%) (V _R =10V, R _L =1kΩ)	t _r		300		ns
Fall time (90%-10%) (V _R =10V, R _L =1kΩ)	t _f		600		ns

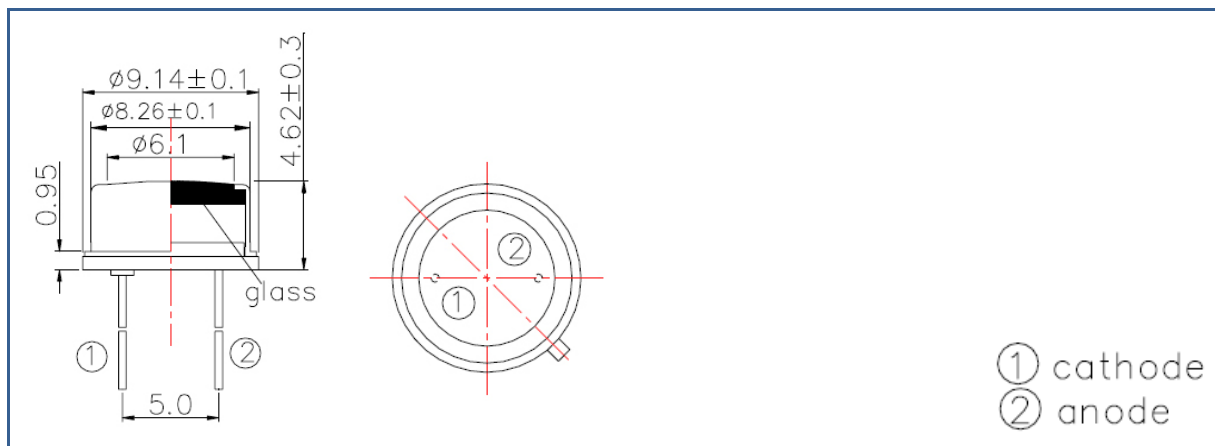




Performance Characteristics



Drawing



Dimensions in mm